# DIPLOMA IN MECHANICAL ENGINEERING (DME) 

# Term-End Examination 

ロロEz3
December, 2016

## BEE-042 : ELECTRONICS

Time: 2 hours
Maximum Marks : 70

Note: Question no. 1 is compulsory. Answer any four of the remaining questions numbered 2 to 8 . Use of scientific calculator is permitted.

1. (a) State True or False for each of the given statements. $7 \times 1=7$
(i) Semiconductors have a large "Forbidden Gap".
(ii) Common emitter current gain $\boldsymbol{\beta}_{\mathrm{dc}}=\mathrm{I}_{\mathrm{B}} / \mathrm{I}_{\mathrm{C}}$.
(iii) An RS latch can be built using NOR or NAND gates.
(iv) The switching action of a gate in an SCR takes place only when the SCR is reverse biased.
(v) In a transistor having finite B , the forward bias across the base-emitter junction is kept constant and the reverse bias across the collector-base junction is increased. In this case, the base current will decrease.
(vi) Piezoelectric transducers combine natural, synthetic and polarized ferroelectric ceramics.
(vii) PROM contains a programmable AND array and a fixed OR array.
(b) Select the correct answer from the given options.
$7 \times 1=7$
(i) According to Boolean algebra, $1+\mathrm{A}+\mathrm{B}+\mathrm{C}=$ (1) A
(2) $\mathrm{A}+\mathrm{B}+\mathrm{C}$
(3) 1
(4) None of these
(ii) Current density J is expressed in terms of the number of electrons per unit volume $n$ (number $/ \mathrm{m}^{2}$ ) and electronic charge $q$ in Coulombs as
(1) $\mathrm{J}=\mathrm{nqE}$
(2) $\mathrm{J}=\mathrm{nE} / \mathrm{q} \mu_{\mathrm{n}}$
(3) $\mathrm{J}=\mathrm{nq} \mu_{\mathrm{n}} \mathrm{E}$

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\begin{equation*}
\mathrm{J}=\mathrm{nq} / \mathrm{E} \tag{4}
\end{equation*}
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(iii) When $\mathbf{P}$ side of a diode is connected to a positive terminal (positive biased)
(1) it offers zero resistance
(2) it offers very low resistance
(3) it offers very high resistance
(4) there is no effect on resistance
(iv) The current through a diode in series with a $1 \mathrm{k} \Omega$ resistor and forward biased using a 5 V battery is
(1) 5 mA
(2) 4 mA
(3) 5 A
(4) $6 \mu \mathrm{~A}$
(v) A half-wave rectifier suffers from the disadvantage of
(1) Excess ripple factor
(2) Low ratio of rectification
(3) Low transformer utilization factor
(4) All of the above
(vi) The decimal equivalent of the binary number 100101 is
(1) 38
(2) 41
(3) 26
(4) 37
(vii) An RS latch can be formed using a combination of
(1) OR and NAND gates
(2) NOR or NAND gates
(3) AND and NOR gates
(4) AND or NOR gates
2. Explain the functioning of a full wave rectifier with the help of a neat diagram. Show that the average value of its output current is twice that of a half-wave rectifier.
3. A bridge rectifier is connected to a $230 \mathrm{~V}, 50 \mathrm{~Hz}$ source voltage and load resistance of $20 \mathrm{k} \Omega$. Calculate :
(a) Output dc voltage
(b) Output dc current
(c) Ripple voltage
(d) Diode rating
4. Draw the circuit diagram for an NPN transistor in CE configuration. Derive an expression for current amplification factor in terms of current gain.
5. Give the truth table for the digital circuit.

6. Explain the concept of working of a thermocouple type pressure gauge.
7. With the help of a neat diagram, explain the working of a CRO.
8. Write short notes on any two of the following : $2 \times 7=14$
(a) Magnetic Recorders
(b) Construction and working of electromagnetic flow meter
(c) Block diagram of monochromatic television transmission and reception circuit

